Revisiting the origin of satellites in core-level photoemission of transparent conducting oxides: The case of n-doped SnO$_2$

Francesco Borgatti, J. A. Berger, Denis Céolin, Jianqiang Sky Zhou, Joshua J. Kas, Matteo Guzzo, C. F. McConville, Francesco Offi, Giancarlo Panaccione, Anna Regoutz, David J. Payne, Jean-Pascal Rueff, Oliver Bierwagen, Mark E. White, James S. Speck, Matteo Gatti, and Russell G. Egdell

1Coniglio Nazionale delle Ricerche – Istituto per lo Studio dei Materiali Nanostrutturati (CNR-ISMN), via P. Gobetti 101, I-40129 Bologna, Italy
2Laboratoire de Chimie et Physique Quantiques, IRSAMC, CNRS, Université Toulouse III - Paul Sabatier, 31062 Toulouse, France
3European Theoretical Spectroscopy Facility (ETSF)
4Synchrotron SOLEIL, L’Orme des Merisiers, Saint-Aubin, BP 48, F-91192 Gif-sur-Yvette, France
5Laboratoire des Solides Irradiés, École Polytechnique, CNRS, École Polytechnique, University of Paris-Saclay, F-91128 Palaiseau, France
6Department of Physics, University of Washington, Seattle, Washington 98195-1560, USA
7Institut für Physik und IRIS Adlershof, Humboldt-Universität zu Berlin, D-12489 Berlin, Germany
8Department of Physics, School of Sciences, RMIT University, Melbourne, Victoria, 3001, Australia
9Dipartimento di Scienze, Università di Roma Tor, 00146 Rome, Italy
10Istituto Officina dei Materiali CNR, Laboratorio TASC, S.S. 14 Km 163.5, AREA Science Park, 34149 Basovizza, Trieste, Italy
11Inorganic Chemistry Laboratory, Department of Chemistry, University of Oxford, South Parks Road, Oxford OX1 3QR, United Kingdom
12Department of Materials, Imperial College London, Exhibition Road, London SW7 2AZ, United Kingdom
13Materials Department, University of California, Santa Barbara, California 93106, USA
14European Synchrotron Radiation Facility, Unité 40129, Bologna, Italy

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The longstanding problem of interpretation of satellite structures in core-level photoemission spectra of metallic systems with a low density of conduction electrons is addressed using the specific example of Sb-doped SnO$_2$. Comparison of ab initio many-body calculations with experimental hard x-ray photoemission spectra of the Sn 4d states shows that strong satellites are produced by coupling of the Sn core hole to the plasma oscillations of the free electrons introduced by doping. Within the same theoretical framework, spectral changes of the valence band spectra are also related to dynamical screening effects. These results demonstrate that, for the interpretation of electron correlation features in the core-level photoelectron spectra of such narrow-band materials, going beyond the homogeneous electron gas electron-plasmon coupling model is essential.

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Transparent conducting oxides (TCOs), such as ZnO, CdO, SnO$_2$, and In$_2$O$_3$, combine optical transparency in the visible region with high electrical conductivity achieved through n-type doping. These features enable a large variety of device applications in optoelectronics and photovoltaics, including their use as transparent electrodes in flat panel displays, organic light-emitting diodes, and solar cells [1–3]. TCOs behave as dilute-electron systems whose density of conduction electrons is much lower than for simple metals, thus offering also an ideal platform to investigate the effects of electronic correlation through the interpretation of the satellite structures occurring in the x-ray photoemission spectra (PES) of core-level and valence states. While it was recognized early on that plasmon satellites invariably accompany the main core-level peaks in the PES of simple metals [4, 5], the interpretation of satellite structures observed for TCOs and other “narrow band” metallic oxides has remained controversial despite the large number of studies [6–14]. After the emission of the photoelectron, as a direct consequence of many-body interactions, the remaining electronic system can be left in different final states giving rise to several lines in the spectrum. Satellites in PES are hence a genuine fingerprint of electronic correlation. In simple metals they were successfully explained on the basis of the homogeneous electron gas (HEG) model as the additional excitation of multiple plasmons [15–18], i.e., quantized charge density oscillations resulting from the long-range nature of the Coulomb interaction. In dilute-electron systems, plasmon energies are typically around 1 eV, which is much smaller than in simple metals and comparable both with the intrinsic core linewidths and with the chemical shifts associated to changes of the oxidation state. Moreover, while in simple metals—as predicted by the HEG model—the overall line shape involves multiple plasmon loss satellites, for the narrow band metals only a single satellite is observed. Therefore, alternative explanations have been put forward, either in terms of mixed valency in the initial state [19], or on the basis of localization of conduction band states by the Coulomb potential of the core hole [6, 7, 20–22].
Solving the ambiguity of the core double-peak structure problem for these systems calls for a joint experimental and theoretical advanced approach. To this end, in the present work we combine hard x-ray photoelectron spectroscopy (HAXPES) with *ab initio* many-body theory to explain the origin of satellites in the core-level spectra of the prototypical undoped and Sb-doped SnO$_2$ TCO. We show that experiments and calculations correlate unambiguously the changes of the valence band (VB) spectrum and the satellite of the core-level Sn 4$d$ peak to the intrinsic plasma oscillations of the free electrons that are introduced by charge carrier doping. The adoption of HAXPES ensures the sensitivity to the electronic structure of the bulk. Since the intensity of the final-state satellite structure in highly correlated metallic oxides strongly depends on the experimental information depth it is, in some cases, only evident throughout HAXPES [23–27]. The calculations combine the GW approximation (GWA) [28] for the self-energy and the cumulant (C) expansion of the Green’s function into the first-principle GW+C scheme [29]. Such an *ab initio* approach, not involving any choice of parameters as in semiempirical models, establishes which of the conflicting interpretations provided up to now is correct, thus solving definitively the debate that has lasted for decades on the effects of carrier doping on the photoemission spectra of transition metal oxides. Moreover, our results further demonstrate that the GW+C method is accurate, predictive, and largely transferable (i.e., not material specific). In fact, this approach has lately been employed in simple metals and semiconductors (including doping effects) [30–40], giving results in very good agreement with experiment. The application of this *ab initio* theory to spectral features of different binding energy (BE) for a typical TCO thus opens the perspective towards the reliable interpretation of electron correlation features in the PES of a large variety of TCO compounds and other conductive oxide materials.

The HAXPES core-level spectra in the O 1$s$, Sn 3$d_{5/2}$, and Sn 4$d$ region of nominally undoped SnO$_2$ and Sb-doped SnO$_2$ samples, grown by plasma assisted molecular beam epitaxy, are shown in Fig. 1. The carrier concentration is $3.8 \times 10^{17}$ cm$^{-3}$ (nominally undoped) and $2.6 \times 10^{20}$ cm$^{-3}$ (doped sample), respectively [41,42]. The spectra were obtained at the GALAXIES beamline of the SOLEIL synchrotron radiation source using hard x rays of about $h\nu = 4$ keV and normal emission detection geometry [43,44]. This condition provides an information depth of about 15 nm, large enough to ensure sensitivity to the electronic structure of the bulk and to minimize the contribution of the surface region. All the spectra for the doped sample exhibit a broadening on the high BE side of the peaks that leads them to have an asymmetric profile, with a small shift to higher binding energy of the BE side of the peaks that leads them to have an asymmetric profile. The fitting analysis of these spectra has been performed consistently with the procedure implemented for previous XPS results [12]. Disentangling the spectral terms by Voigt functions in all cases shows a single peak for the undoped sample and two peaks separated by 0.78 eV (O 1$s$) and 0.53 eV (Sn 3$d_{5/2}$) for the doped one, while the shallow 4$d$ spectrum can be fitted by one or two Voigt pairs with a spin-orbit splitting energy of 1.09 eV and with an additional weak contribution from the O 2$s$ level, in agreement with previous XPS results for this and other TCOs [12,14,45]. Further details of the

![FIG. 1. (a) Scheme of the final-state configurations for the (S)screened and (U)unscreened channels according to the Kotani-Toyazawa models [20,22]. (b)–(d) Core-level HAXPES spectra of O 1$s$, Sn 3$d_{5/2}$, and Sn 4$d$ for nominally undoped SnO$_2$ (bottom) and Sb-doped SnO$_2$ (top), respectively. The background of the spectra has been subtracted using a Shirley profile.](5)
where $\epsilon^H$ is the Hartree energy. In the GWA, the self-energy $\Sigma^{G}(\omega)$ is the convolution of the Green's function $G(\omega)$ and the dynamically screened Coulomb interaction $W(\omega) = \epsilon^{-1}(\omega)\nu_\epsilon$, with $\nu_\epsilon$ being the bare Coulomb interaction that is screened by the inverse dielectric function $\epsilon^{-1}(\omega)$. Since in the GWA $\text{Im}\Sigma^{G}(\omega)$ is proportional to the loss function $-\text{Im}\epsilon^{-1}(\omega)$, the cumulant $C_i(t)$ describes the dynamical screening of the hole $\epsilon_i$ through the coupling with the bosonic charge excitations $\omega_s$, which are the plasmons and many-body interband transitions appearing as peaks in the loss function. Therefore, the first term in Eq. (1) yields the QP peak located at $\epsilon_i$, while the exponential of $C_i(t)$ in (1) generates satellite structures at multiples of the bosonic energies $\omega_s$ away from the QP peak. In the past, the $A_i(\omega)$ of core levels have been extensively obtained using model approaches [5,22]. In Ref. [16] Langreth demonstrated that for an isolated core level the cumulant expansion (2) yields the exact solution of the electron-boson model in the specific case of the HEG. On the other hand, Kotani and Toyazawa [20] took into account the screening of the core hole by adopting a single-impurity Anderson model consisting of a localized state and conduction electrons. Instead, in the ab initio calculations for SnO$_2$ we can now make direct use of the band-structure information for the real system. Doping is simulated by adding a HEG-type free-carrier contribution in the calculation of $\epsilon^{-1}(\omega)$. To consider the doping dependence, the free-carrier concentration is similar to the experimental value as well as larger by one order of magnitude. All the calculations presented in the following were convoluted by a Gaussian function to account for the experimental resolution (see Supplemental Material [46]). We note that the calculated spectra include a Lorentzian broadening due to the imaginary part of the self-energy. The convolution of Gaussian and Lorentzian line shapes supports the adoption of the Voigt function for the spectral analysis.

The numerical results for the Sn 4$d$ core level are shown in Fig. 2 in which the QP contributions have also been singled out [47]. The spin-orbit coupling is not included in the calculations; hence only a single peak is present. Noticeably, in the undoped case (black curves) the full spectral function coincides with the QP-only part: all the structures in the spectrum are hence exclusively due to QP excitations. Upon doping the QP contributions remain the same and only a small shift of about 0.05 eV is found. Doping mostly affects the incoherent part of the spectral function: through a change of the dynamical screening $\epsilon^{-1}(\omega)$, it induces a modification of electronic correlations beyond the QP picture. Within the GW+C framework this correlation effect can be understood in terms of coupling of core hole and neutral excitations. In order to trace its origin, we have hence also calculated the loss function $-\text{Im}\epsilon^{-1}(\mathbf{q},\omega)$ (inset of Fig. 2 for the $\mathbf{q} \rightarrow 0$ limit). For a finite carrier density we find a new plasmon peak in the loss function at an energy corresponding to the separation between the QP and the new incoherent structures in the spectral function. Conversely, the loss function of a homogeneous electron gas with a density equal to the carrier concentration of doped SnO$_2$ provides a plasmon peak shifted to the much higher energy of about 1.4 eV (see Supplemental Material [46]). Hence we can safely conclude that the broadening of the Sn 4$d$ spectrum for the doped SnO$_2$ is the fingerprint of the correlation effect coupling the 4$d$ photoelectrons with the collective oscillation of the free carriers introduced in the material by doping. This mechanism should also be effective for the other core-level spectra in Fig. 1, although they cannot be simulated with our pseudopotential approach.

In Fig. 2 we have also investigated what happens in the calculated spectral function when the doping level is changed. According to the expectations based on the weak-coupling limit of the HEG model [16], the intrinsic plasmon satellite intensity for an isolated core level should increase as the conduction electron density $n_c$ decreases [18,48]. At variance with these expectations, the intensity of the satellite decreases and merges with the QP broad structure making it hardly discernible. Moreover, in the ab initio calculations at most only one satellite is clearly visible in the spectra in agreement with HAXPES results, rather than a series of multiple plasmon satellites as predicted by the HEG model. These results therefore show that, in order to capture the satellite structures for narrow-band materials, it is essential to go beyond the HEG electron-plasmon coupling model Hamiltonian [15,16] and to perform ab initio calculations that are materials specific.

The support for this conclusion comes through the close matching of theoretical and experimental results. To this aim, in Fig. 3 the Sn 4$d$ HAXPES spectra have been aligned to the maximum of the Sn 4$d_{5/2}$ peak to manifest more explicitly the broadening on the high BE side of the spectrum for doped SnO$_2$ after the subtraction of the Shirley background and of the O 2s contribution close to the low BE side of the region. The spectra are compared to the $d$-orbital projection of the spectral functions ($d$-PSF) for which the spin-orbit splitting has been phenomenologically included by adding the same curve shifted for the experimental spin-orbit value (1.09 eV) and scaled to achieve the statistical branching ratio of $d$ doublets. Despite the implicit rough approximations of this treatment,
FIG. 3. Comparison of HAXPES Sn 4d spectra (bottom) and d-orbital projection (d-PSF) of the spectral functions (top) for undoped and doped SnO$_2$. All curves are aligned to the position of the experimental Sn 4d$_{5/2}$ term.

the qualitative agreement with experiment is very good, especially considering that extrinsic effects, due to inelastic losses of the outgoing photoelectrons, and their interference with intrinsic contributions, are not included in the calculations [5,49].

Further, in Fig. 4 we consider the valence band (VB) spectra which, for both the pure and the doped compounds, display a three-peaked structure (A–C) in agreement with XPS data previously reported [12]. For the undoped sample, the onset of the valence band maximum (VBM) is placed through linear extrapolation at about 3.84 eV BE relative to the Fermi level $E_F$, slightly larger than the quoted bulk band gap of 3.62 eV [51]. On the low BE side, the spectra have a weak but well-defined feature (D) that tails into the bulk band gap, which was interpreted as a contribution from lone-pair Sn 5s states occurring at the sample surface and, for the doped sample, concerns also Sb 5s-5p states [52]. Looking at the position of the stronger features (A), the spectrum of the Sb-doped SnO$_2$ is shifted to higher BE by 0.27 eV, and the shift of the conduction states below $E_F$ is clearly visible as well as the broadening of the tail (T) on the high BE side. The comparison of the VB states with the calculated spectral function, whose angular-projected contributions have been weighted by the correspondent values of the photoionization cross sections [50], shows that the calculations provide correctly all the relevant features of the experimental VB spectra: (i) the position of the main peaks with respect to the valence band maximum, (ii) the broadening induced by the free-carrier doping, and (iii) the enhancement of the asymmetric tail at the bottom of the valence band. The latter, in particular, confirms Hedin’s predictions based on the HEG for valence electrons [53]. In the past, asymmetric tails have often been modeled for core levels using ad hoc Doniach-Sunjic or Mahan line shapes [5,54,55]. In the present case, instead, this result emerges consistently from the same ab initio framework that is used for both the Sn 4d states and the VB. Thus, as for the satellite of the Sn 4d core line, this tail can be associated with dynamical screening effects requiring to go beyond a single-particle picture. This is a direct consequence of the frequency dependence of $\text{Im} \Sigma''(\omega)$ [17,18,53], which is related to the presence of low-energy ($\sim 1–2$ eV) density fluctuations that couple with high-energy QP excitations in the photoemission spectra [33,56]. On the other hand, the relative intensity of spectral features A–C does not match the experimental results properly, although the slightly larger reduction of B-C vs A with increasing doping is qualitatively reproduced. This mismatch might be partially ascribed, besides the intrinsic correlation effects, to the method adopted to account for the dependence of the photoemission process on the photon energy and polarization, which, in principle, should be included through explicit calculation of the matrix elements within the one-step model of photoemission. This theoretical approach is quite complicated and clearly beyond the scope of this work. However, the weighting of the angular-projected terms by the photoionization cross sections improves the agreement with the experiment significantly (see Supplemental Material [46]). These results confirm the
reliability of this approach and will surely stimulate further efforts to get a better agreement among the theory and the experiment.

In conclusion, we have elucidated the origin of the satellite structure observed in the Sn 4$d$ core-level photoemission spectrum of Sb-doped SnO$_2$ by comparing experimental measurements to results obtained from \textit{ab initio} many-body theory. We have demonstrated that such a satellite is produced by the coupling of the Sn 4$d$ core electrons to the plasma oscillation of the free electrons introduced in the material by doping. Moreover, within the same theoretical framework we were able to explain also the enhancement of the asymmetric tail in the valence band photoemission spectrum of doped SnO$_2$. These results demonstrate that, in order to capture the satellite structures for narrow-band materials and identify properly the underlying electronic structure excitations, it is essential to go beyond the HEG electron-plasmon coupling model and to perform material-specific \textit{ab initio} calculations. In this perspective, the results for the Sb-doped SnO$_2$ TCO suggest that the GW+C theory can be a very promising approach for the interpretation of electron correlation features in the PES spectra of several conductive oxide materials.

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[47] The calculated spectral functions have been aligned to their valence band maximum and not to the Fermi level, as in the experiment, since the work function cannot be determined in calculations for the bulk. Moreover, the binding energy for shallow Sn 4d core levels could be improved by QP self-consistency and inclusion of vertex corrections [68–70]; however, this is not crucial for the present work.


